

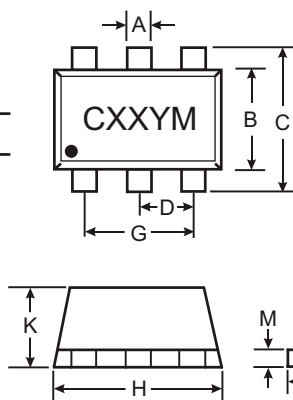
COMPLEMENTARY NPN/PNP PRE-BIASED SMALL SIGNAL SOT-563 DUAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Lead-Free Device

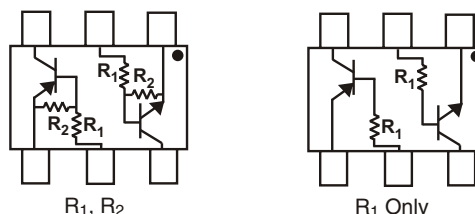
Mechanical Data

- Case: SOT-563, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208 (Note 1)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (approx.)



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.15	0.25	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

P/N	R1	R2	MARKING
DCX124EH	22KΩ	22KΩ	C17
DCX144EH	47KΩ	47KΩ	C20
DCX143EH	4.7KΩ	4.7KΩ	C08
DCX114YH	10KΩ	47KΩ	C14
DCX123JH	2.2KΩ	47KΩ	C06
DCX114EH	10KΩ	10KΩ	C13
DCX143TH	4.7KΩ	-	C07
DCX114TH	10KΩ	-	C12



SCHEMATIC DIAGRAM, TOP VIEW

Maximum Ratings NPN Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-10 to +40 -10 to +40 -10 to +30 -6 to +40 -5 to +12 -10 to +40 -5 V _{max} -5 V _{max}	V
Output Current	I _O	30 30 100 70 100 50 100 100	mA
Output Current	I _C (Max)	100	mA
Power Dissipation (Total)	P _d	150	mW
Thermal Resistance, Junction to Ambient Air (Note 2)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Note:
1. If lead-bearing terminal plating is required, please contact your Diodes Inc. sales representative for availability and minimum order details.
 2. Mounted on FR4 Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.

Maximum Ratings PNP Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH DCX143TH DCX114TH	V _{IN}	+10 to -40 +10 to -40 +10 to -30 +6 to -40 +5 to -12 +10 to -40 +5 Vmax +5 Vmax	V
Output Current DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH DCX143TH DCX114TH	I _O	-30 -30 -100 -70 -100 -50 -100 -100	mA
Output Current All	I _C (Max)	-100	mA
Power Dissipation (Total)	P _d	150	mW
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics NPN Section @ T_A = 25°C unless otherwise specified

Characteristic (DDC143TH & DDC114TH only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50	—	—	V	I _C = 50μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	—	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	—	—	V	I _E = 50μA
Collector Cutoff Current	I _{CBO}	—	—	0.5	μA	V _{CB} = 50V
Emitter Cutoff Current	I _{EBO}	—	—	0.5	μA	V _{EB} = 4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	0.3	V	I _C /I _B = 2.5mA / 0.25mA I _C /I _B = 1mA / 0.1mA DCX143TH DCX114TH
DC Current Transfer Ratio	h _{FE}	100	250	600	—	I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product*	f _T	—	250	—	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{I(off)}	0.5 0.5 0.5 0.3 0.5 0.5	1.1 1.1 1.1 — — 1.1	—	V	V _{CC} = 5V, I _O = 100μA
Input Voltage DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{I(on)}	—	1.9 1.9 1.9 — — 1.9	3.0 3.0 3.0 1.4 1.1 3.0	V	V _O = 0.3V, I _O = 5mA V _O = 0.3V, I _O = 2mA V _O = 0.3V, I _O = 20mA V _O = 0.3V, I _O = 1mA V _O = 0.3V, I _O = 5mA V _O = 0.3V, I _O = 10mA
Output Voltage DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	V _{O(on)}	—	0.1	0.3	V	I _O /I _I = 10mA / 0.5mA I _O /I _I = 10mA / 0.5mA I _O /I _I = 10mA / 0.5mA I _O /I _I = 5mA / 0.25mA I _O /I _I = 5mA / 0.25mA I _O /I _I = 10mA / 0.5mA
Input Current DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	I _I	—	—	0.36 0.18 1.8 0.88 3.6 0.88	mA	V _I = 5V
Output Current	I _{O(off)}	—	—	0.5	μA	V _{CC} = 50V, V _I = 0V
DC Current Gain DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	G _I	56 68 20 68 80 30	—	—	—	V _O = 5V, I _O = 5mA V _O = 5V, I _O = 5mA V _O = 5V, I _O = 10mA V _O = 5V, I _O = 10mA V _O = 5V, I _O = 10mA V _O = 5V, I _O = 5mA

* Transistor - For Reference Only

Electrical Characteristics PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic (DCX143TH & DCX114TH only)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-50	—	—	V	$I_C = -50\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-50	—	—	V	$I_C = -1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	$I_E = -50\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	—	-0.5	μA	$V_{CB} = -50\text{V}$
Emitter Cutoff Current	I_{EBO}	—	—	-0.5	μA	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	-0.3	V	$I_C/I_B = 2.5\text{mA} / 0.25\text{mA}$ DCX143TH $I_C/I_B = 1\text{mA} / 0.1\text{mA}$ DCX114TH
DC Current Transfer Ratio	h_{FE}	100	250	600	—	$I_C = -1\text{mA}$, $V_{CE} = -5\text{V}$
Gain-Bandwidth Product*	f_T	—	250	—	MHz	$V_{CE} = -10\text{V}$, $I_E = 5\text{mA}$, $f = 100\text{MHz}$

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	$V_{I(off)}$	-0.5 -0.5 -0.5 -0.3 -0.5 -0.5	-1.1 -1.1 -1.1 — — -1.1	—	V	$V_{CC} = -5\text{V}$, $I_O = -100\mu\text{A}$
	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	$V_{I(on)}$	—	-1.9 -1.9 -1.9 — — -1.9	-3.0 -3.0 -3.0 -1.4 -1.1 -3.0		$V_O = -0.3\text{V}$, $I_O = -5\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -2\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -20\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -1\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -5\text{mA}$ $V_O = -0.3\text{V}$, $I_O = -10\text{mA}$
Output Voltage	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	$V_{O(on)}$	—	-0.1	-0.3	V	$I_O/I_I = -10\text{mA} / -0.5\text{mA}$ $I_O/I_I = -10\text{mA} / -0.5\text{mA}$ $I_O/I_I = -10\text{mA} / -0.5\text{mA}$ $I_O/I_I = -5\text{mA} / -0.25\text{mA}$ $I_O/I_I = -5\text{mA} / -0.25\text{mA}$ $I_O/I_I = -10\text{mA} / -0.5\text{mA}$
Input Current	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	I_I	—	—	-0.36 -0.18 -1.8 -0.88 -3.6 -0.88	mA	$V_I = -5\text{V}$
Output Current		$I_{O(off)}$	—	—	-0.5	μA	$V_{CC} = 50\text{V}$, $V_I = 0\text{V}$
DC Current Gain	DCX124EH DCX144EH DCX143EH DCX114YH DCX123JH DCX114EH	G_I	56 68 20 68 80 30	—	—	—	$V_O = -5\text{V}$, $I_O = -5\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$ $V_O = -5\text{V}$, $I_O = -10\text{mA}$ $V_O = -5\text{V}$, $I_O = -10\text{mA}$ $V_O = -5\text{V}$, $I_O = -10\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$
Gain-Bandwidth Product*		f_T	—	250	—	MHz	$V_{CE} = -10\text{V}$, $I_E = -5\text{mA}$, $f = 100\text{MHz}$

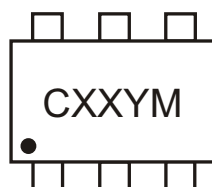
* Transistor - For Reference Only

Ordering Information (Note 3)

Device	Packaging	Shipping
DCX124EH-7	SOT-563	3000/Tape & Reel
DCX144EH-7	SOT-563	3000/Tape & Reel
DCX143EH-7	SOT-563	3000/Tape & Reel
DCX114YH-7	SOT-563	3000/Tape & Reel
DCX123JH-7	SOT-563	3000/Tape & Reel
DCX114EH-7	SOT-563	3000/Tape & Reel
DCX143TH-7	SOT-563	3000/Tape & Reel
DCX114TH-7	SOT-563	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



CXX = Product Type Marking Code (See Page 1)

YM = Date Code Marking

Y = Year ex: P = 2003

M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009
Code	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

TYPICAL CURVES - DCX143EH NPN SECTION

NEW PRODUCT

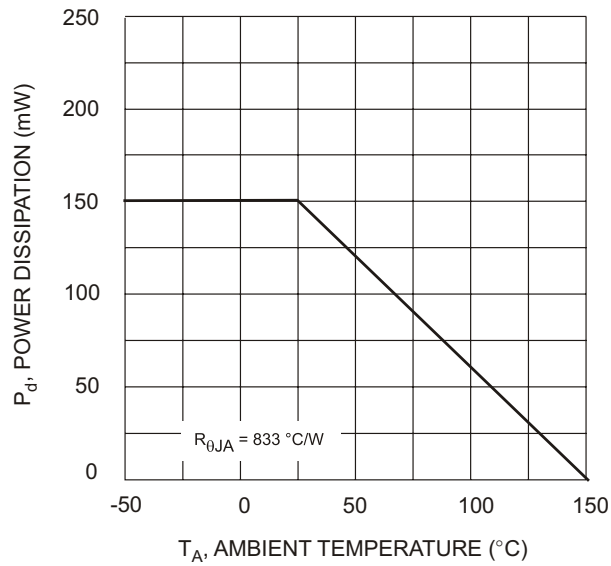


Fig. 1 Derating Curve - Total

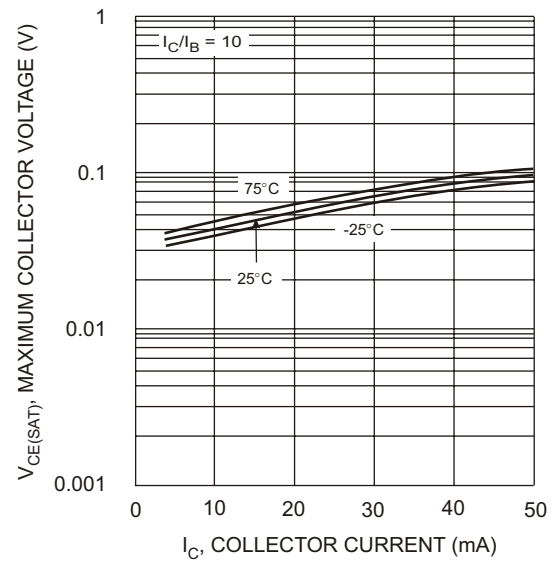


Fig. 2 $V_{CE(SAT)}$ vs. I_C

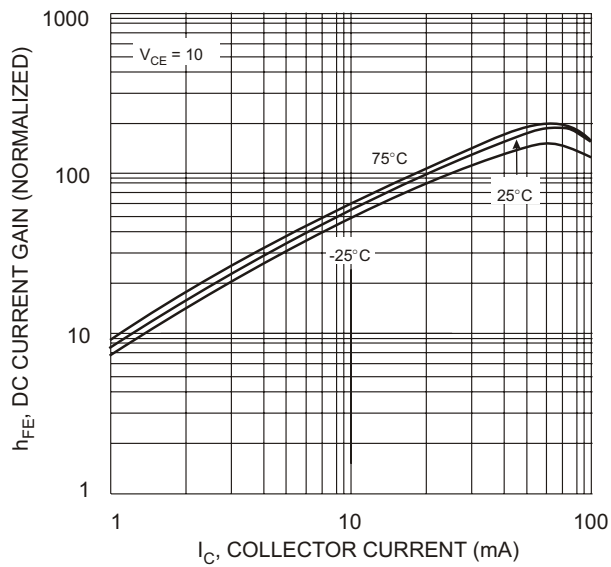


Fig. 3 DC CURRENT GAIN

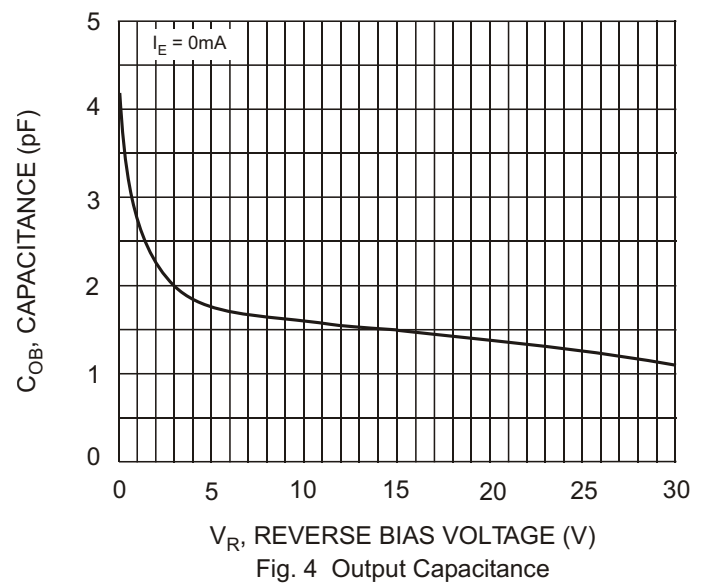


Fig. 4 Output Capacitance

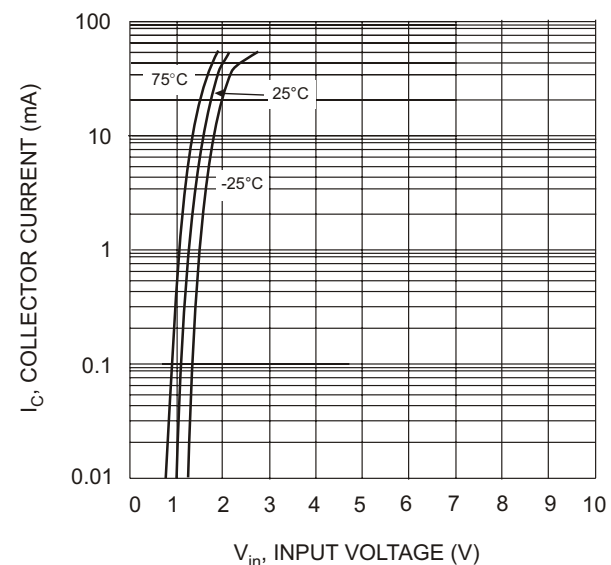


Fig. 5 Collector Current Vs. Input Voltage

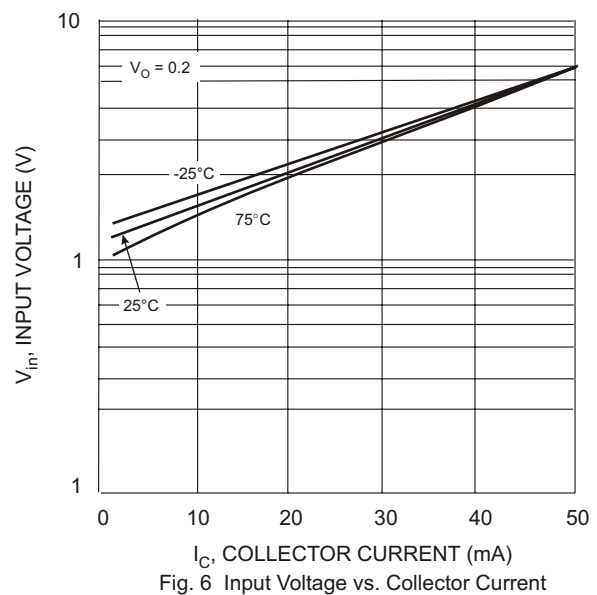


Fig. 6 Input Voltage vs. Collector Current

TYPICAL CURVES - DCX143EH PNP SECTION
